

## **BC212LB**

### **PNP General Purpose Amplifier**

- This device is designed for general purpose amplifier application at collector currents to 100mA. WWW.DZSC.
- Sourced from process 68.



1. Emitter 2. Collector 3. Base

### **Absolute Maximum Ratings\*** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	100	mA
T <sub>J.</sub> T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Characteristics						
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 2mA$	50			V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A$	60			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10μA	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 30V			15	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 4V			15	nA
On Chara	cteristics*					
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 10\mu A$ $V_{CE} = 5V, I_{C} = 2mA$	40 60		45.4	46
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$			0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA			1.4	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = 5V$ , $I_{C} = 2mA$	0.6		0.72	V
Small Sig	nal Characteristics	ACT LIE				
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> = 10V, f = 1MHz			6	pF
h <sub>FE</sub>	Small Signal Current Gain	$V_{CE} = 5V$ , $I_C = 2mA$ , $f = 1KHz$	60			
NF	Noise Figure	$V_{CE} = 5V$ , $I_{C} = 200\mu A$ , $f = 1KHz$ $R_{G} = 2K\Omega$ , $BW = 200Hz$			10	dB

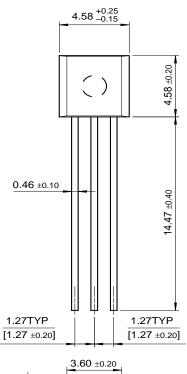
\* Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

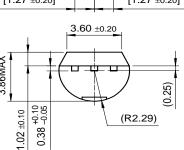
These ratings are based on a maximum junction temperature of 150°C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

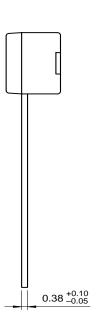
Thermal Characteristics TA=25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient 357 °C.		°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case 125		°C/W

# **Package Dimensions**

TO-92







Dimensions in Millimeters

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EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franc	hise™	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
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